TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSVI)

## 2SK3767

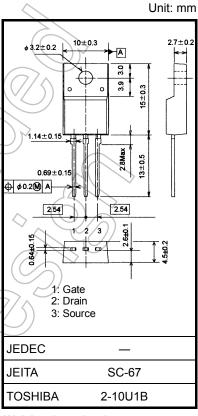
#### **Switching Regulator Applications**

- Low drain-source ON resistance:  $R_{DS (ON)} = 3.3 \Omega (typ.)$
- High forward transfer admittance: |Y<sub>fs</sub>| = 1.6 S (typ.)
- Low leakage current:  $I_{DSS} = 100 \mu A (V_{DS} = 600 V)$
- Enhancement mode:  $V_{th}$  = 2.0 to 4.0 V ( $V_{DS}$  = 10 V,  $I_D$  = 1 mA)

# Unit

## Absolute Maximum Ratings (Ta = 25°C)

| Characteristics                                      |       | Symbol   | Rating             | Unit        |     |
|--|-------|----------|--------------------|-------------|-----|
| Drain-source voltage                                 |       |          | $V_{DSS}$          | 600         | V   |
| Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ ) |       |          | $V_{DGR}$          | 600         | A   |
| Gate-source voltage                                  |       |          | V <sub>GSS</sub>   | <u>±</u> 30 | > v |
| Drain current  | DC    | (Note 1) | ID                 | 2           |     |
|  | Pulse | (Note 1) | I <sub>DP</sub>    | 5           | A   |
| Drain power dissipation (Tc = 25°C)                  |       |          | PD                 | 25          | /w  |
| Single pulse avalanche energy (Note 2)               |       |          | EAS                | 93          | mJ  |
| Avalanche current                                    |       |          | IAR                | 2           | Α   |
| Repetitive avalanche energy (Note 3)                 |       |          | (E <sub>AR</sub> ) | 4           | Lm/ |
| Channel temperature                                  |       |          | Teh                | 150         | °C  |
| Storage temperature range                            |       |          | T <sub>stg</sub>   | -55~150     | °C  |



Weight: 1.7 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### **Thermal Characteristics**

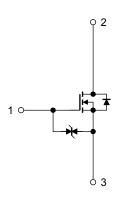
| Characteristics                        | Symbol                 | Max  | Unit |
|--|------------------------|------|------|
| Thermal resistance, channel to case    | Rth (ch-c)             | 5.0  | °C/W |
| Thermal resistance, channel to ambient | R <sub>th (ch-a)</sub> | 62.5 | °C/W |

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD} = 90 \text{ V}$ ,  $T_{ch} = 25^{\circ}\text{C}$  (initial), L = 41mH,  $R_G = 25 \Omega$ ,  $I_{AR} = 2 \text{ A}$ 

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Please handle with caution.



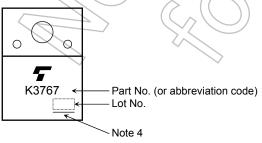
#### **Electrical Characteristics (Ta = 25°C)**

| Characteristics              |               | Symbol               | Test Condition  | Min | Тур. | Max | Unit |
|------------------------------|---------------|----------------------|---|-----|------|-----|------|
| Gate leakage curr            | ent           | I <sub>GSS</sub>     | $V_{GS} = \pm 25 \text{ V}, V_{DS} = 0 \text{ V}$                       | _   | _    | ±10 | μΑ   |
| Gate-source break            | kdown voltage | V (BR) GSS           | $I_G = \pm 10 \ \mu A, \ V_{DS} = 0 \ V$                                | ±30 | _    |     | V    |
| Drain cut-off curre          | nt            | I <sub>DSS</sub>     | V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V                          | /_  | _    | 100 | μΑ   |
| Drain-source brea            | kdown voltage | V (BR) DSS           | $I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$                             | 600 | _    |     | V    |
| Gate threshold voltage       |               | V <sub>th</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA                           | 2.0 | ) /_ | 4.0 | V    |
| Drain-source ON resistance   |               | R <sub>DS</sub> (ON) | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 1 A                            | 7   | 3.3  | 4.5 | Ω    |
| Forward transfer a           | dmittance     | Y <sub>fs</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 A                            | 0.8 | 1.6  |     | S    |
| Input capacitance            |               | C <sub>iss</sub>     |   | _   | 320  |     |      |
| Reverse transfer capacitance |               | C <sub>rss</sub>     | V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz                | 7   | 30   |     | pF   |
| Output capacitance           |               | C <sub>oss</sub>     |   | _   | 100  |     |      |
| Switching time               | Rise time     | t <sub>r</sub>       | 10 V   ID=1A  |     | 15   |     |      |
|                              | Turn-on time  | t <sub>on</sub>      | V <sub>GS</sub> Output  | ((  | 55   | ) — |      |
|                              | Fall time     | t <sub>f</sub>       | Σ 200 Ω   | 7   | 20   | _   | ns   |
|                              | Turn-off time | t <sub>off</sub>     | Duty ≤ 1%, $t_W = 10 \mu s$ $V_{DD} \simeq 200 \text{ V}$               |     | 80   |     |      |
| Total gate charge            |               | Qg                   |   | ) — | 9    | _   |      |
| Gate-source charge           |               | Qgs                  | $V_{DD} \simeq 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 2 \text{ A}$ | _   | 5    | _   | nC   |
| Gate-drain charge            |               | Qgd                  |   |     | 4    | _   |      |

### Source-Drain Ratings and Characteristics (Ta = 25°C)

| Characteristics                           | Symbol             | Test Condition                                | Min | Тур. | Max  | Unit |
|---|--------------------|---|-----|------|------|------|
| Continuous drain reverse current (Note 1) | )) I <sub>DR</sub> |   | _   | _    | 2    | Α    |
| Pulse drain reverse current (Note 1)      | I <sub>DRP</sub>   | ((//)) -                                      | _   | _    | 5    | Α    |
| Forward voltage (diode)                   | V <sub>DSF</sub>   | I <sub>DR</sub> = 2 A, V <sub>GS</sub> = 0 V  | _   | _    | -1.7 | V    |
| Reverse recovery time                     | trr                | $I_{DR} = 2 \text{ A}, V_{GS} = 0 \text{ V},$ | _   | 1000 | _    | ns   |
| Reverse recovery charge                   | Q <sub>rr</sub>    | dl <sub>DR</sub> /dt = 100 A/μs               | _   | 3.5  | _    | μС   |



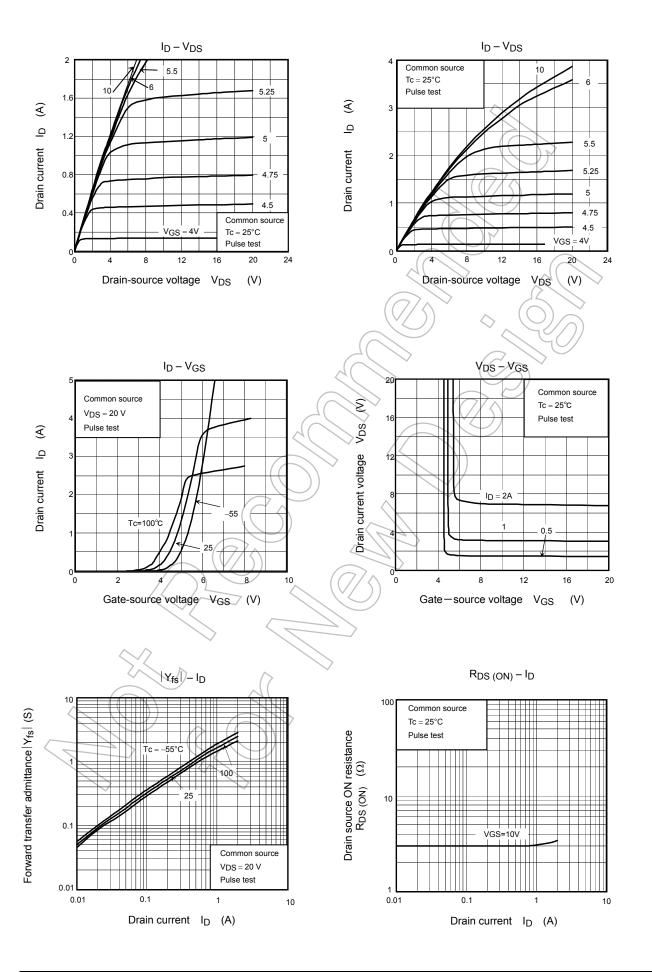


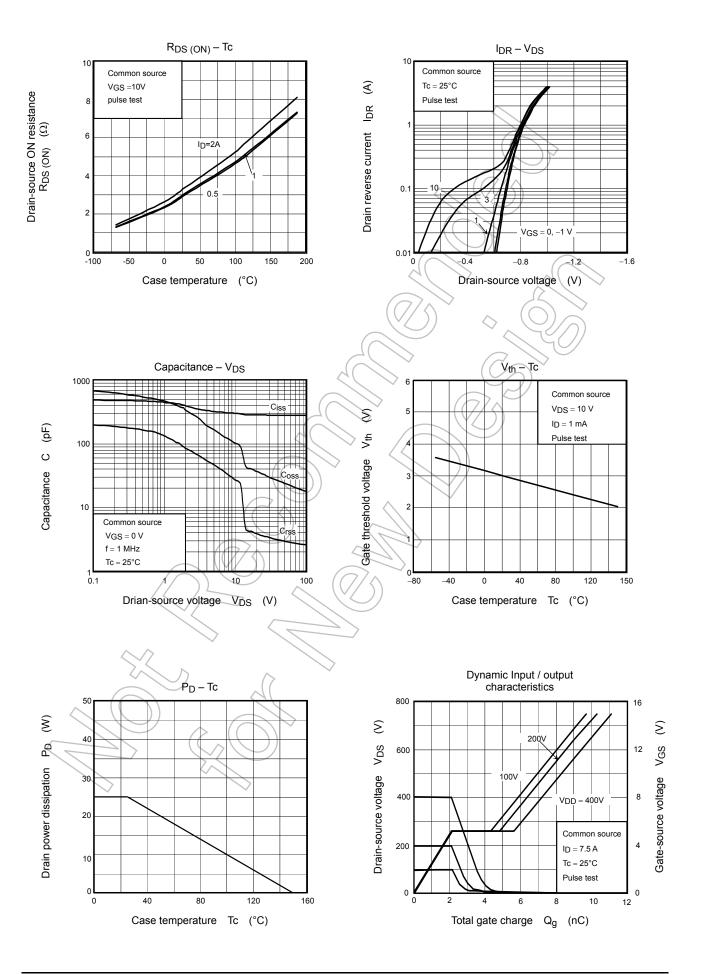
Note 4: A line under a Lot No. identifies the indication of product Labels.

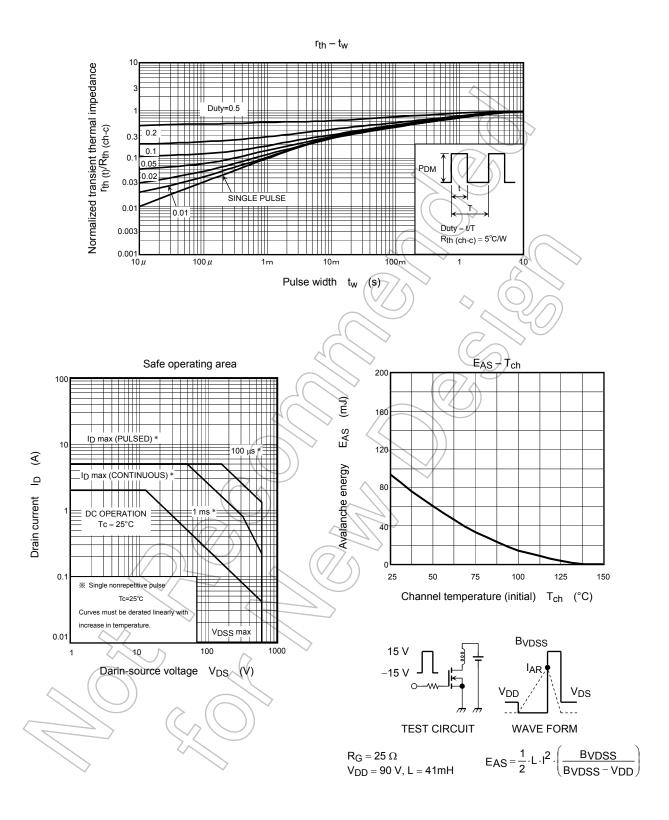
Not underlined: [[Pb]]/INCLUDES > MCV

 $\label{thm:compatible} \mbox{Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]}$ 

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